

FORM PTO-1449  
(Rev. 2-32)U.S. Department of Commerce  
Patent and Trademark Office

Atty. Docket No.

Serial No.

05-720-US1

10/559,979

INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT

(Use several sheets if necessary)

Applicant:

Kouvetakis, et al.

Filing Date:

December 8, 2005

Group:

2814

## U.S. PATENT DOCUMENTS

Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate
82	1.	US 2003-0157787 A1	August 21, 2003	Murthy, et al.			
	2.	US 2006-0134895 A1	June 22, 2006	Kouvetakis, et al.			
	3.	US 2006-0236923 A1	October 26, 2006	Kouvetakis, et al.			
	4.	6,911,084	June 28, 2005	Kouvetakis, et al.			
	5.	5,532,183	July 2, 1996	Sugawara, et al.			
	6.	5,198,387	March 30, 1993	Tang, et al.			
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	9.	6,723,621	April 20, 2004	Cordone, et al.			
	10.	6,897,471	May 24, 2005	Soref, et al.			
52	11.	6,441,716	August 27, 2002	Doppalapudi, et al.			

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Examiner Initial	Document Number	Date	Country	Class	Subclass	Translation	
						Yes	No

EXAMINER

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SM	12.	WO 2005/001902	January 6, 2005	PCT				
	13.	WO 2004/114368	December 29, 2004	PCT				
	14.	WO 2005/015609	February 17, 2005	PCT				
	15.	WO 2003/033781	April 24, 2003	PCT				
g	16.	WO 2006/009171	January 26, 2006	PCT				

**OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc).**

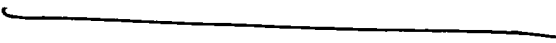
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CA	50.	D. E. Wingeleth, A. D. Norman, "Redistribution of primary silyl- and germylphosphines; synthesis of trisilyl- and trigermylphosphines", Phosphorus Sulfur, 39(1-2), pp. 123-129, (1988).
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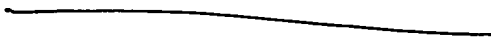
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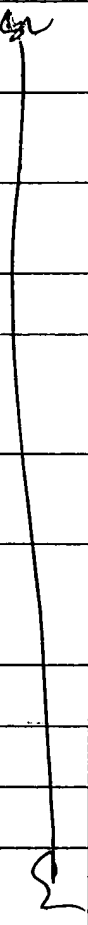
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<b>FORM PTO-1449</b> (Rev. 2-32)	<b>U.S. Department of Commerce</b> <b>Patent and Trademark Office</b>	<b>Atty. Docket No.</b> 05-720-US1	<b>Serial No.</b> 10/559,979
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (Use several sheets if necessary)		<b>Applicant:</b> Kouvetakis, et al.	
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## COMMONLY OWNED CO-PENDING APPLICATIONS

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2	1.	Kouvetakis, et al., U.S. Patent Application No. 10/559,980, Filed on December 8, 2005.
5	2.	Kouvetakis, et al., U.S. Patent Application No. 10/559,981, Filed on September 5, 2006 (Projected Publication date is January 11, 2007).

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